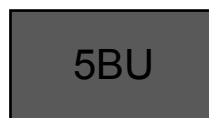


Features

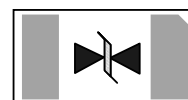
100Watts peak pulse power ($t_p = 8/20\mu s$)
Tiny DFN1006 package
Bidirectional configurations
Solid-state silicon-avalanche technology
Low clamping voltage
Low leakage current
Low capacitance ($C_j = 0.3pF$ typ. IO to IO)
IEC 61000-4-2 $\pm 20kV$ contact $\pm 20kV$ air
IEC 61000-4-4 (EFT) 40A $5/50ns$
IEC 61000-4-5 (Lightning) 4.5A ($8/20\mu s$)

Applications

Cell Phone Handsets and Accessories
Microprocessor based equipment
Personal Digital Assistants (PDA's)
Notebooks, Desktops, and Servers
Portable Instrumentation



DFN1006-2L(Pb-Free)



Schematic Diagram

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{pp}	100	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	4.5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	20 20	kV
Lead Soldering Temperature	T_L	260(10seconds)	$^{\circ}C$
Junction Temperature	T_J	-55 to + 125	$^{\circ}C$
Storage Temperature	T_{stg}	-55 to + 125	$^{\circ}C$

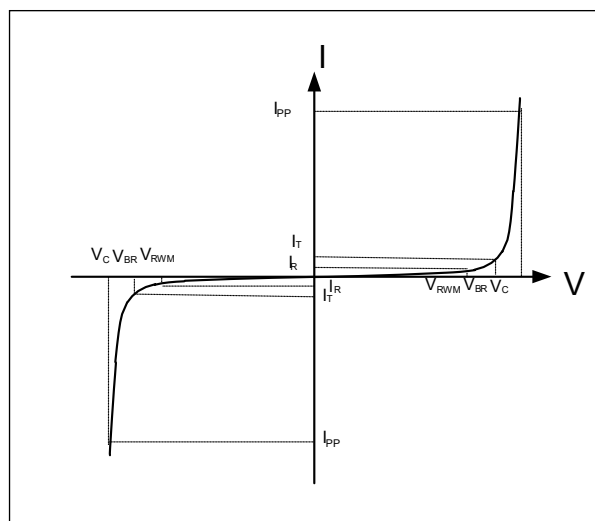
Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				5.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0			V
Reverse Leakage Current	I_R	$V_{RWM}=5V, T=25^{\circ}C$			100	nA
Peak Pulse Current	I_{PP}	$t_p=8/20\mu s$			4.0	A
Clamping Voltage	V_C	$I_{PP}=4.5A, t_p=8/20\mu s$			20	V
Junction Capacitance	C_j	IO to IO $V_R=0V, f=1MHz$		0.3		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

Note: 8/20μs pulse waveform.



Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)

Figure 1: Peak Pulse Power vs. Pulse Time

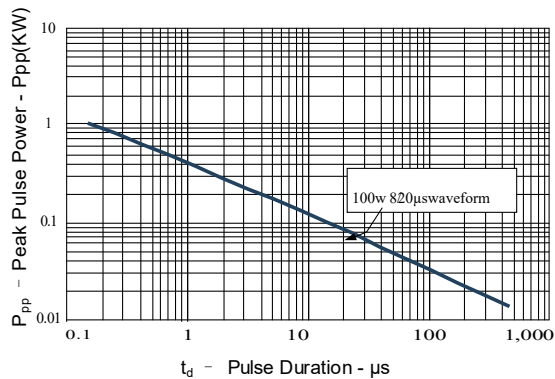


Figure 2: Power Derating Curve

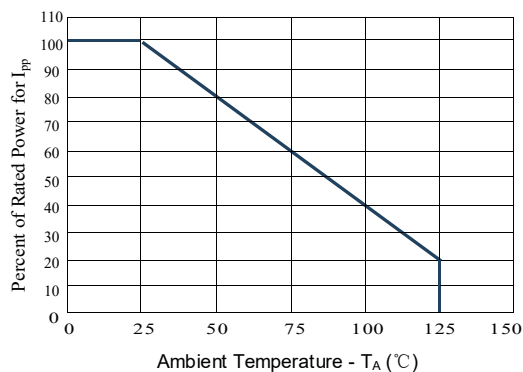


Figure3: Pulse Waveform

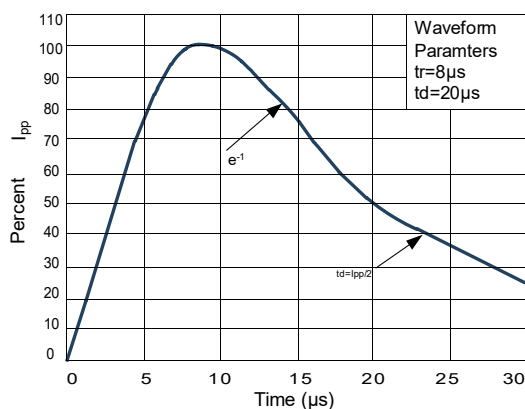


Figure 4: Clamping Voltage vs. Ipp

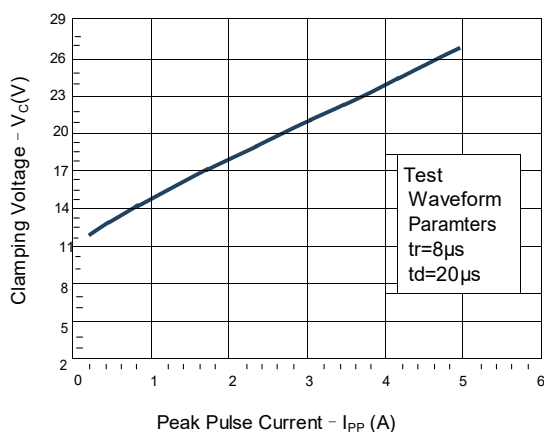


Figure5: Positive Clamping voltage (TLP)

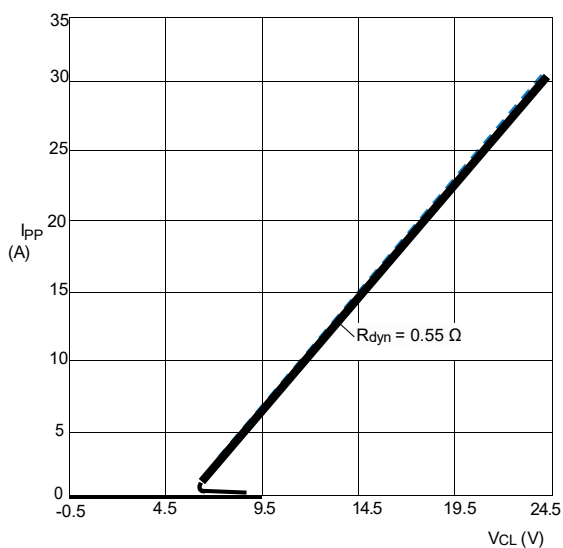
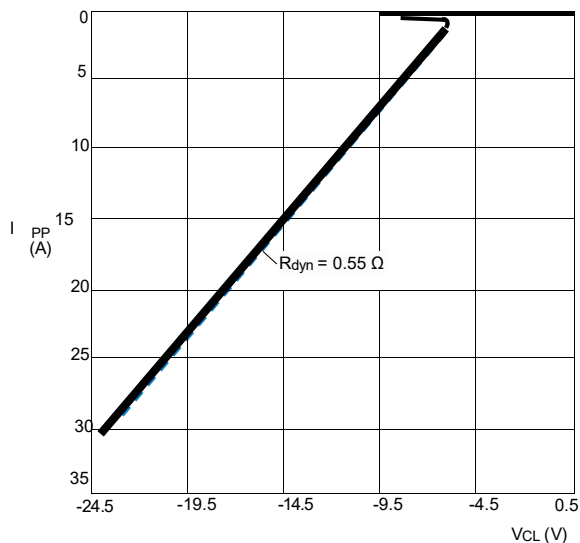
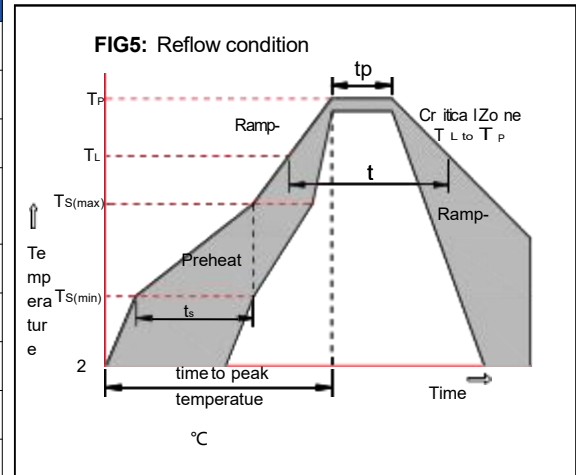


Figure5: Negative Clamping voltage (TLP)



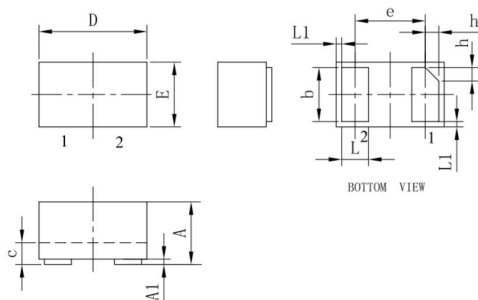
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C



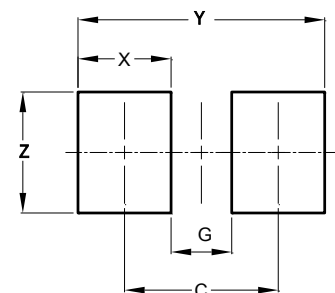
Package Dimensions & Suggested Pad Layout

DFN1006-2L



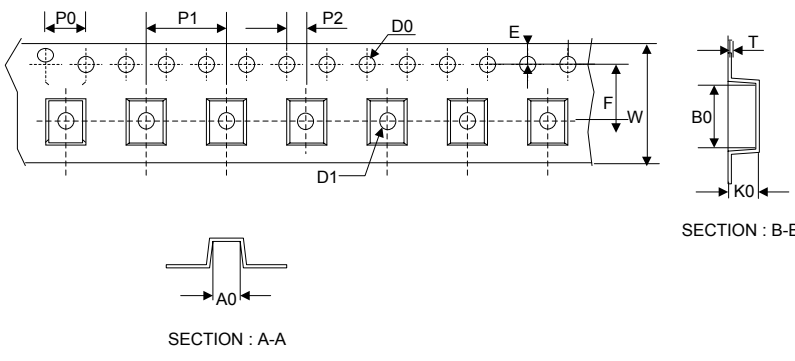
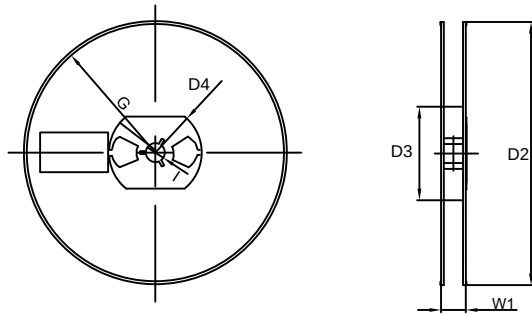
DFN1006-2L

	Millimeters			Inches		
	Min. (mm)	Typ. (mm)	Max. (mm)	Min. (mm)	Typ. (mm)	Max. (mm)
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.59BSC			0.026BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.25	0.30	0.35	0.010	0.012	0.013
L1	0.05REF			0.002REF		
h	0.07	0.12	0.17	0.003	0.005	0.007



Dimensions	Value (in mm)
C	0.70
G	0.30
X	0.40
Y	1.10
Z	0.65

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.20
		P1	2.00±0.20
		P2	1.55±0.20
		D0	1.55±0.20
		D1	0.40±0.20
		E	1.55±0.25
		F	3.60±0.20
		W	8.00±0.20
		A0	1.00±0.20
		B0	1.40±0.20
		K0	0.75±0.20
		T	0.20±0.20
		D2	177.0±5.0
		D3	55Min.
		D4	R24.6±2.0
7" Reel		G	R82.0±2.0
		I	13.0±2.0
		W1	10.20±3.0
		Quantity: 3000PCS	